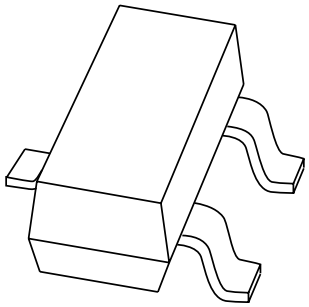
DATA SHEET



BSR12
PNP switching transistor

Product specification

1999 Jul 23

Philips
Semiconductors

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PNP switching transistor BSR12

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 15 V).

APPLICATIONS

- High-speed, saturated switching applications for industrial service in thick and thin-film circuits.

DESCRIPTION

PNP switching transistor in a SOT23 plastic package.

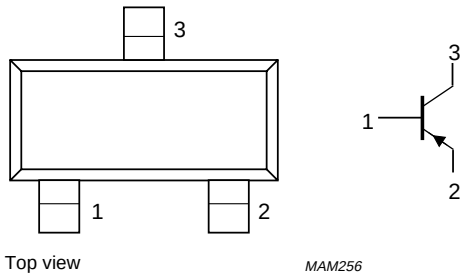


Fig.1 Simplified outline (SOT23) and symbol.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

MARKING

TYPE NUMBER	MARKING CODE
BSR12	B5p

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–15	V
V_{CEO}	collector-emitter voltage	open base	–	–15	V
I_{CM}	peak collector current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	250	mW
T_j	junction temperature		–	150	°C
h_{FE}	DC current gain	$I_C = -10$ mA; $V_{CE} = -1$ V	30	–	
		$I_C = -50$ mA; $V_{CE} = -1$ V	30	120	
f_T	transition frequency	f = 500 MHz; $I_C = -50$ mA; $V_{CE} = -10$ V	1.5	–	GHz
t_{off}	turn-off time	$I_{Con} = -30$ mA; $I_{Bon} = -3$ mA; $I_{Boff} = 3$mA	–	30	ns

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–15	V
V_{CEO}	collector-emitter voltage	open base	–	–15	V
V_{EBO}	emitter-base voltage	open collector	–	–3	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on a ceramic substrate $8 \times 10 \times 0.7$ mm.

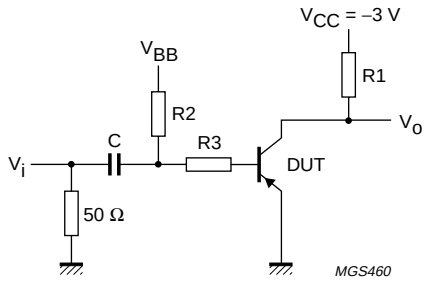
CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = –10 V	–	–	–50	nA
		I_E = 0; V_{CB} = –10 V; T_{amb} = 125 °C	–	–	–5	µA
I_{CES}	collector cut-off current	V_{BE} = 0; V_{CE} = –10 V	–	–	–50	nA
$V_{(BR)CBO}$	breakdown voltage	I_E = 0; I_C = –10 µA	–15	–	–	V
$V_{(BR)CES}$	breakdown voltage	V_{BE} = 0; I_C = –10 µA	–15	–	–	V
$V_{(BR)EBO}$	breakdown voltage	I_C = 0; I_E = –100 µA	–3	–	–	V
$V_{CEOsust}$	collector-emitter sustaining voltage	I_B = 0; I_C = –10 mA	–15	–	–	V
V_{CEsat}	collector-emitter saturation voltage	I_C = –10 mA; I_B = –1 mA; note 1	–	–	–130	mV
		I_C = –50 mA; I_B = –5 mA; note 1	–	–180	–270	mV
		I_C = –100 mA; I_B = –10 mA; note 1	–	–	–450	mV
V_{BEsat}	base-emitter saturation voltage	I_C = –10 mA; I_B = –1 mA; note 1	–725	–	–920	mV
		I_C = –50 mA; I_B = –5 mA; note 1	–800	–	–1150	mV
		I_C = –100 mA; I_B = –10 mA; note 1	–900	–	–1500	mV
h_{FE}	DC current gain	I_C = –1 mA; V_{CE} = –1 V; note 1	30	–	–	
		I_C = –10 mA; V_{CE} = –1 V; note 1	30	–	–	
		I_C = –50 mA; V_{CE} = –1 V; note 1	30	–	120	
		I_C = –50 mA; V_{CE} = –1 V; T_{amb} = 55 °C; note 1	30	–	–	
		I_C = –100 mA; V_{CE} = –1 V; note 1	20	–	–	
f_T	transition frequency	IC = –50 mA; V_{CE} = –10 V; f = 500 MHz	1.5	–	–	GHz
C_c	collector capacitance	I_E = I_e = 0; V_{CB} = –5 V	–	–	4.5	pF
C_e	emitter capacitance	I_C = I_c = 0; V_{EB} = –0.5 V	–	–	6	pF
Switching time (see Fig.2)						
t_{on}	turn-on time	V_i = –6.85 V; V_{BB} = 0 V; I_{Con} = –30 mA; I_{Bon} = –3.0 mA	–	–	20	ns
t_{off}	turn-off time	V_i = 11.7 V; V_{BB} = –9.85 V; I_{Con} = –30 mA; I_{Bon} = –3 mA; I_{Boff} = 3 mA	–	–	30	ns

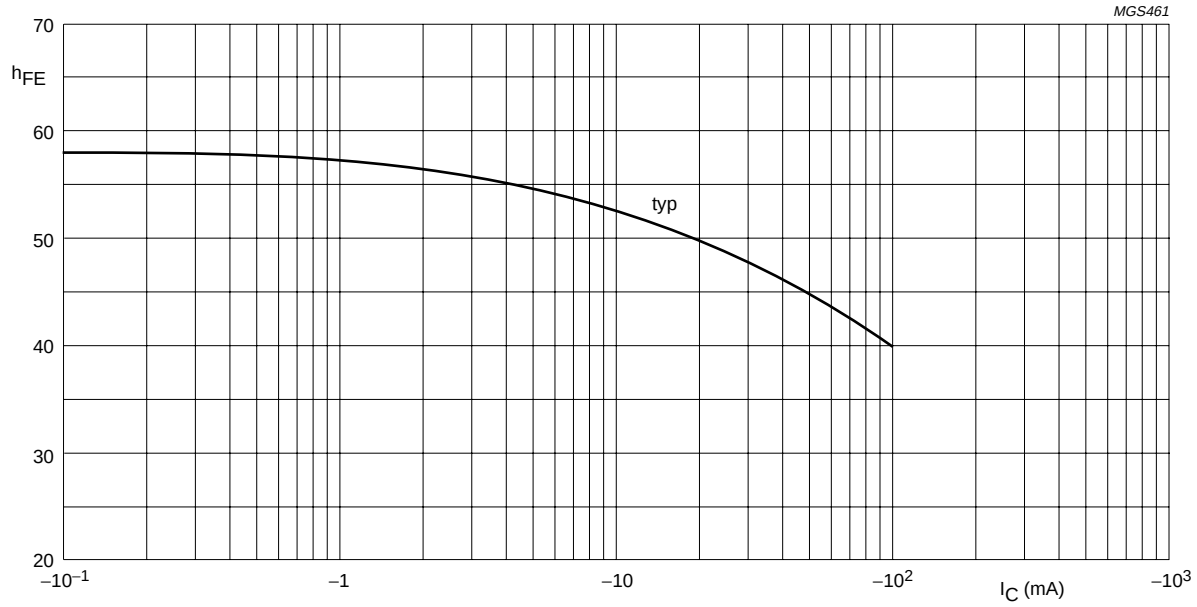
Note

1. Pulse test: t_p = 300 µs; δ = 0.01.



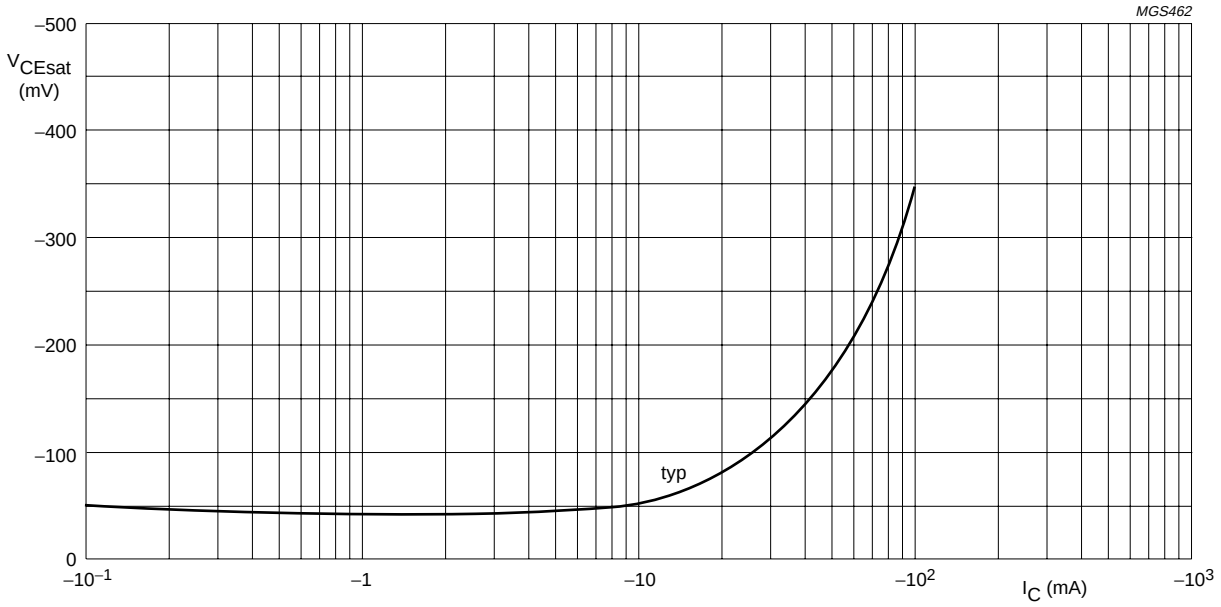
R1 = 94 Ω; R2 = 1 kΩ; R3 = 2 kΩ; C = 0.1 μF.
Pulse generator: Pulse duration t_p = 400 ns. Rise time t_r < 1 ns. Output impedance Z_O = 50 Ω.
Sampling scope: Rise time t_r < 1 ns. Input impedance Z_i = 100 kΩ.

Fig.2 Test circuit for switching times.



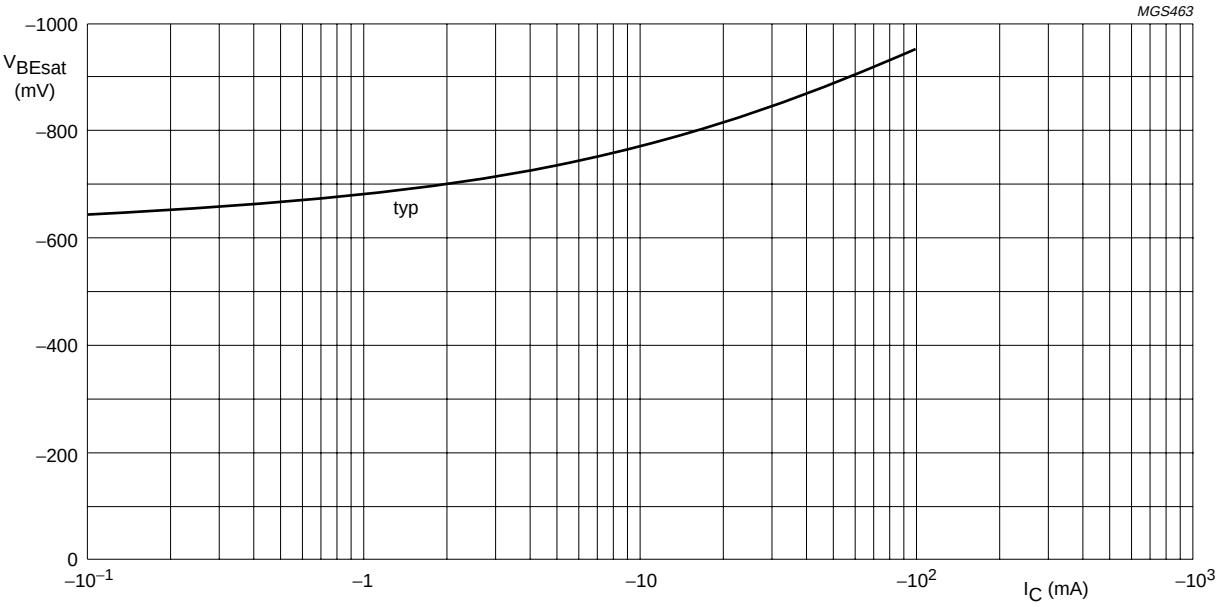
V_{CE} = – 1 V; T_{amb} = 25°C.

Fig.3 DC current gain; typical values.



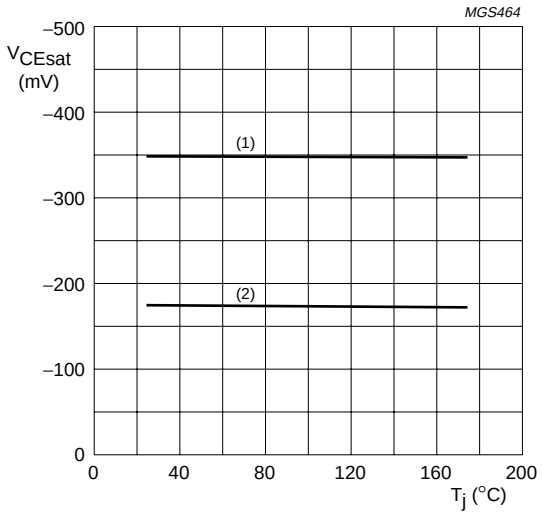
$I_C/I_B = 10.$

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



$I_C/I_B = 10.$

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.



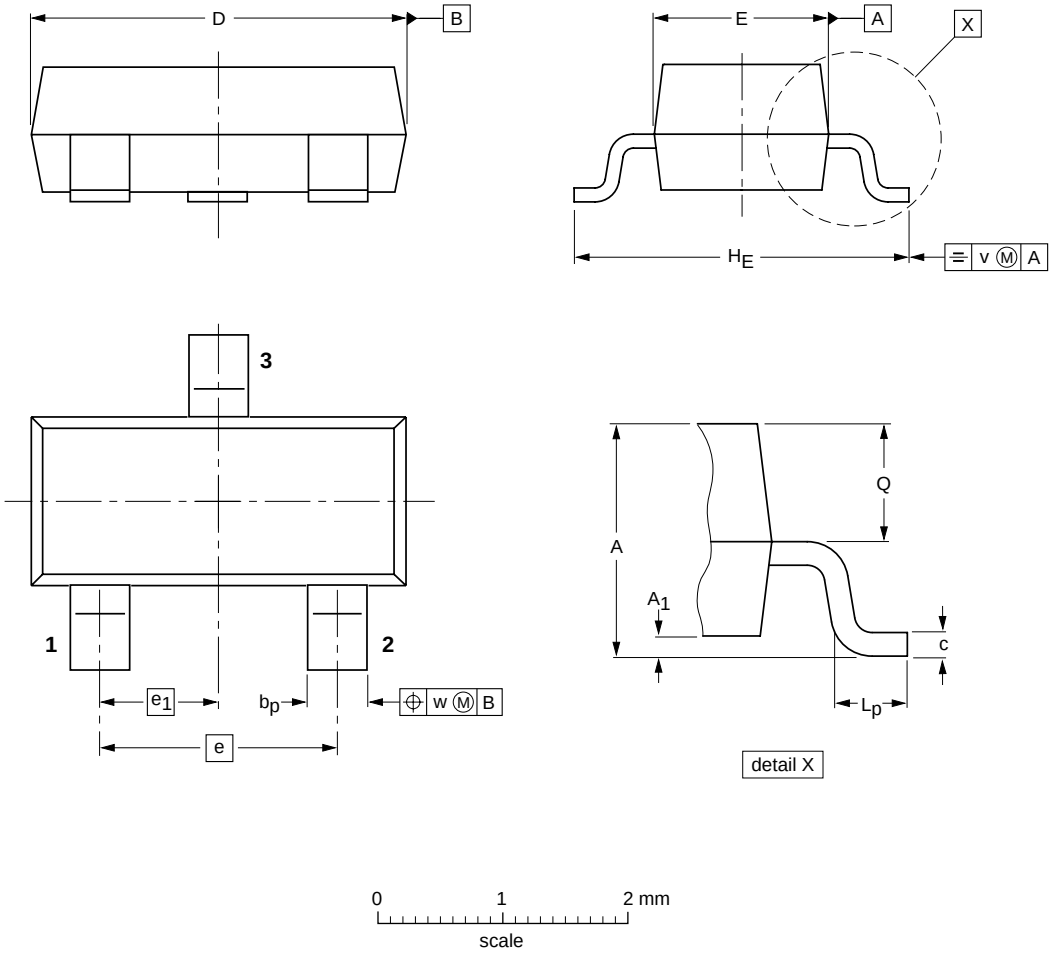
(1) I_C = 100 mA; I_B = 10 mA

(2) I_C = 50 mA and I_B = 5 mA.

Fig.6 Collector-emitter saturation voltage as a function of junction temperature; typical values.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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NOTES

NOTES

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